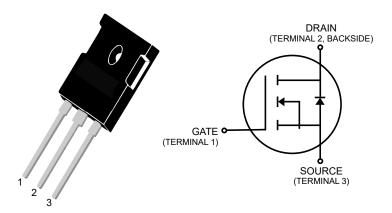
1200V, 360 mΩ N-Channel mSiC[™] MOSFET

MSC360SMA120B



Product Overview

1200V, 360 m Ω typical at V_{GS} = 20V, 413 m Ω typical at V_{GS} = 18V, Silicon Carbide (SiC) N-Channel MOSFET, TO-247.



Features

- AEC-Q101 qualified option available
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, T_{I(max)} = 175 °C
- · Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

Benefits

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- · Eliminates the need for external freewheeling diode
- · Lower system cost of ownership

Applications

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- · Smart grid transmission and distribution
- · Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of this device.

1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain source voltage	1200	V
I _D	Continuous drain current at T _C = 25 °C	12	Α
	Continuous drain current at T _C = 100 °C	8	
I _{DM}	Pulsed drain current ¹	27	
V_{GS}	Gate-source voltage	23 to -10	V
	Transient gate-source voltage	25 to -12	
P _D	Total power dissipation at T _C = 25 °C	90	W
	Linear derating factor	0.60	W/°C

Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Тур.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	_	1.29	1.67	°C/W
Tj	Operating junction temperature	-55	_	175	°C
T _{STG}	Storage temperature	-55	_	175	
T _L	Lead temperature for 10 seconds	_	_	300	°C
τ_{M}	Mounting torque, M3 screw for heat sink attachment (requires 1, not included)	_	0.8	_	N·m
Wt	Package weight	_	6.2	-	g

ESD practices should comply with JESD-625.

1.2 Electrical Performance

The following table shows the static characteristics of this device. T_J = 25 °C unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$V_{GS} = 0V, I_D = 100 \mu A$	1200	_	_	V
R _{DS(on)}	Drain-source on resistance ¹	V _{GS} = 20V, I _D = 5A	_	360	450	mΩ
		$V_{GS} = 18V, I_D = 5A$	_	413	_	
V _{GS(th)}	Gate-source threshold voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	1.9	3.0	5.0	V
I _{DSS}	Zero gate voltage drain current	V _{DS} = 1200V, V _{GS} = 0V	_	0.1	20	μΑ
		V _{DS} = 1200V, V _{GS} = 0V, T _J = 175 °C	_	1.0	_	
I _{GSS}	Gate-source leakage current	V _{GS} = 20V/–10V		_	±100	nA



Note:

1. Pulse test: pulse width < 380 μ s, duty cycle < 2%.

The following table shows the dynamic characteristics of this device. T_J = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating V_{GS} = 20V/–5V.

Table 1-4. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V	_	258	_	pF
C _{rss}	Reverse transfer capacitance	V _{DD} = 1200V	_	2.0	_	
C _{oss}	Output capacitance	$V_{AC} = 25 \text{ mV}$ f = 200 kHz	_	28	_	
Q_{G}	Total gate charge	V _{GS} = -5V/20V	_	21	_	nC
Q _{GS}	Gate-source charge	V _{DD} = 800V	_	6.0	_	
Q_{GD}	Gate-drain charge	$I_D = 5A$	_	7.0	_	
t _{d(on)}	Turn-on delay time	V _{DD} = 850V	_	14	_	ns
t _r	Voltage rise time	$V_{GS} = -5V/20V$	_	15	_	
t _{d(off)}	Turn-off delay time	I _D = 10A	_	16	_	
t _f	Voltage fall time	$R_{G(ext)} = 16\Omega$	_	19	_	
E _{on}	Turn-on switching energy	Freewheeling diode = MSC360SMA120B (V _{GS} = -5V);	_	400	_	μJ
E _{off}	Turn-off switching energy	reference Figure 1-19	_	34	_	
ESR	Gate equivalent series resistance	f = 1 MHz, 25 mV, drain short	_	3.4	_	Ω
SCWT	Short circuit withstand time	$V_{DS} = 960V, V_{GS} = 20V$	_	2.6	_	μs
E _{AS}	Avalanche energy, single pulse	I _D = 5A		100	_	mJ

The following table shows the body diode characteristics of this device. $T_J = 25$ °C unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 5A$, $V_{GS} = 0V$	_	4.0	_	V
		$I_{SD} = 5A$, $V_{GS} = -5V$	_	4.2	5.0	
t _{rr}	Reverse recovery time	I_{SD} = 7A, V_{GS} = -5V, Drive R_G = 16 Ω , V_{DD} = 850V, dI/dt = -5420 A/ μ s	_	39	_	ns
Q _{rr}	Reverse recovery charge		_	119	_	nC
I _{RRM}	Reverse recovery current		_	8.0	_	Α



1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs. V_{DS} at T_{J}

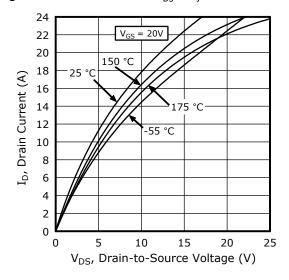


Figure 1-2. Drain Current vs. V_{DS} at V_{GS}

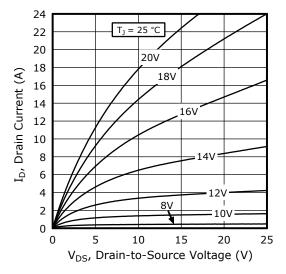


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}

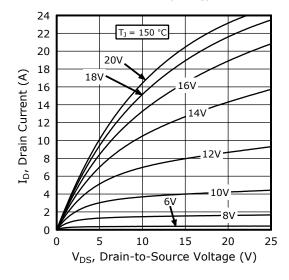


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}

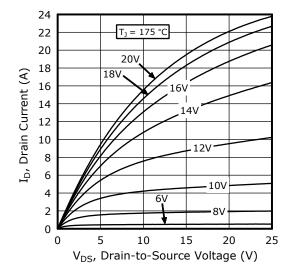




Figure 1-5. R_{DS(on)} vs. Junction Temperature

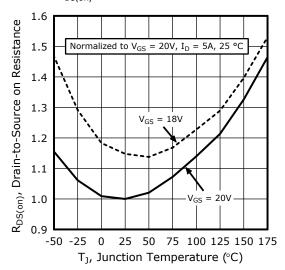


Figure 1-6. Gate Charge Characteristics

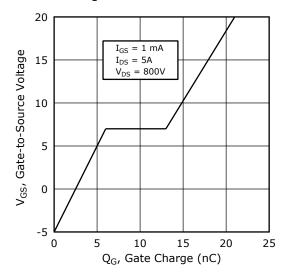


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

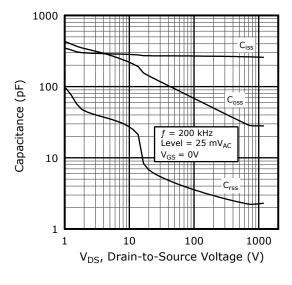


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

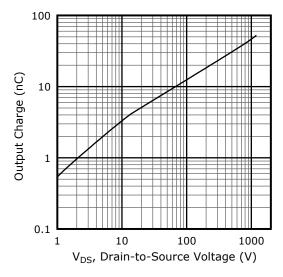




Figure 1-9. Output Stored Energy vs. V_{DS}

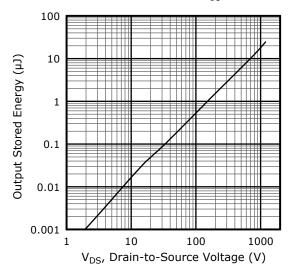


Figure 1-10. I_D vs. V_{DS} 3rd Quadrant Conduction

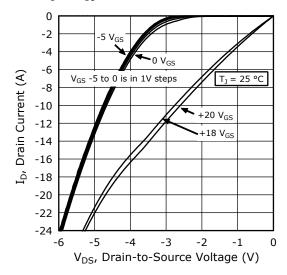


Figure 1-11. I_D vs. V_{DS} 3rd Quadrant Conduction

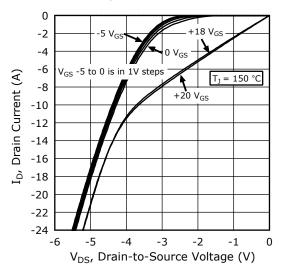


Figure 1-12. Switching Energy E_{on} vs. $V_{DS} \& I_{D}$

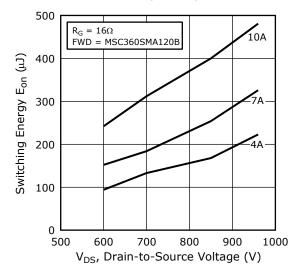




Figure 1-13. Switching Energy E_{off} vs. $V_{DS} \& I_{D}$

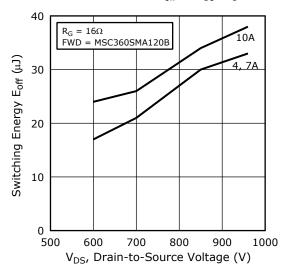


Figure 1-14. Switching Energy vs. R_G

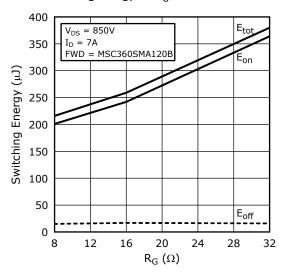


Figure 1-15. Switching Energy vs. Junction Temperature

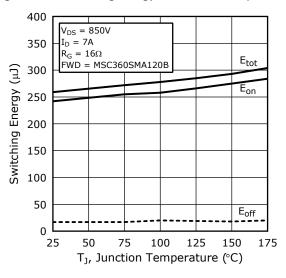


Figure 1-16. Threshold Voltage vs. Junction Temperature

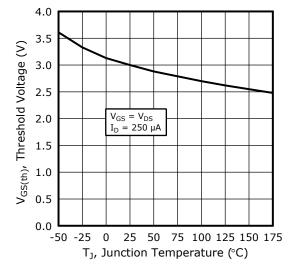




Figure 1-17. Forward Safe Operating Area

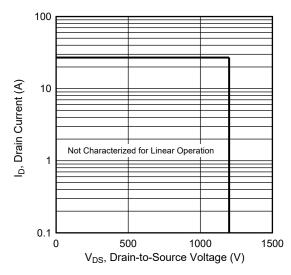
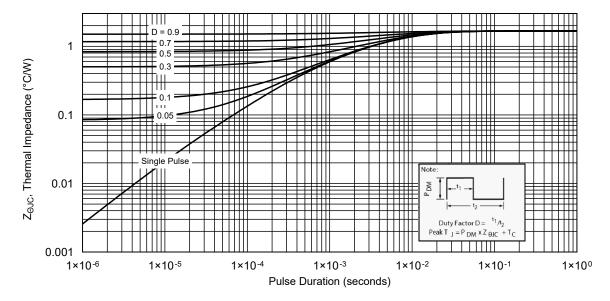
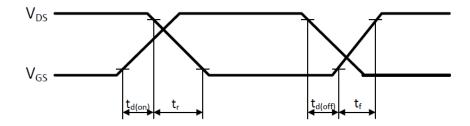


Figure 1-18. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-19. Switching Waveform





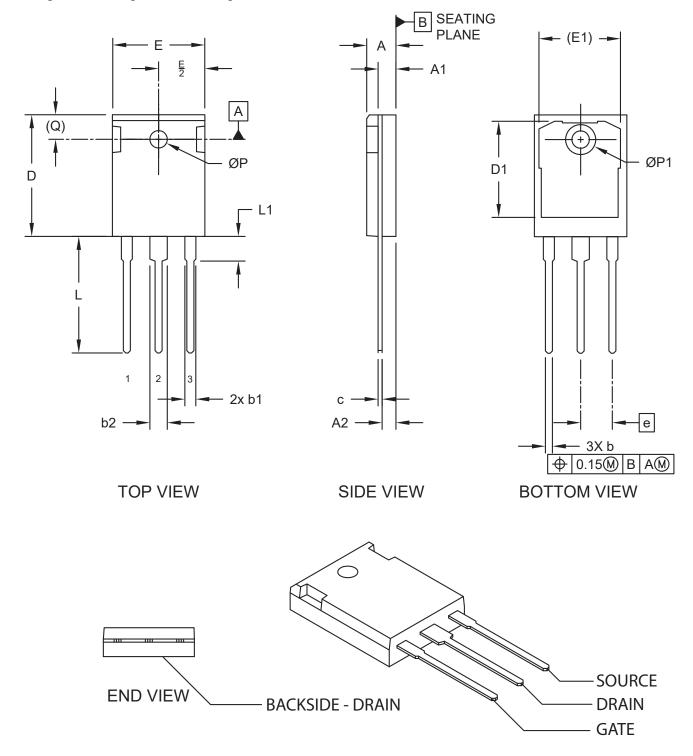
2. Package Specification

This section shows the package specification of this device.

2.1 Package Outline Drawing

The following figure illustrates the TO-247 package outline of this device.

Figure 2-1. Package Outline Drawing





The following table shows the TO-247 dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. TO-247 Dimensions

Symbol	Description	Min. (mm)	Max. (mm)
N	Number of leads	3	·
е	Pitch	5.44 BSC	
Α	Overall height	4.70	5.31
A1	Tab height	1.50	2.49
A2	Seating plane to lead	2.21	2.59
b	Lead width	1.02	1.40
b1	Lead shoulder width (X2)	1.65	2.41
b2	Lead shoulder width	2.87	3.38
С	Lead thickness	0.41	0.79
L	Lead length	19.81	20.32
L1	Lead shoulder length	3.99	4.50
D	Molded body length	20.80	21.46
D1	Thermal pad length	16.25	17.65
Е	Total width	15.49	16.26
E1	Thermal pad width	13.10	14.50
Q	Hole center to tab edge	6.15 REF	
ØP	Hole diameter	3.51	3.81
ØP1	Thermal pad hole diameter	7.18 REF	

Notes:

Dimensioning and tolerancing per ASME Y14.5M.

- BSC: Basic dimension. Theoretically exact value shown without tolerances.
- REF: Reference dimension, usually without tolerance, for information purposes only.



3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description	
D	07/2024	Added τ_M symbol for mounting torque in Table 1-2.	
С	05/2024	The following changes are made in this revision the document:	
		• Updated values in Table 1-1, Table 1-2, Table 1-3, Table 1-4, and Table 1-5.	
		• Updated 1.3. Typical Performance Curves and 2.1. Package Outline Drawing.	
В	07/2021	Updated test condition value for E _{AS} in Table 1-4.	
A	04/2021	Document created.	



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